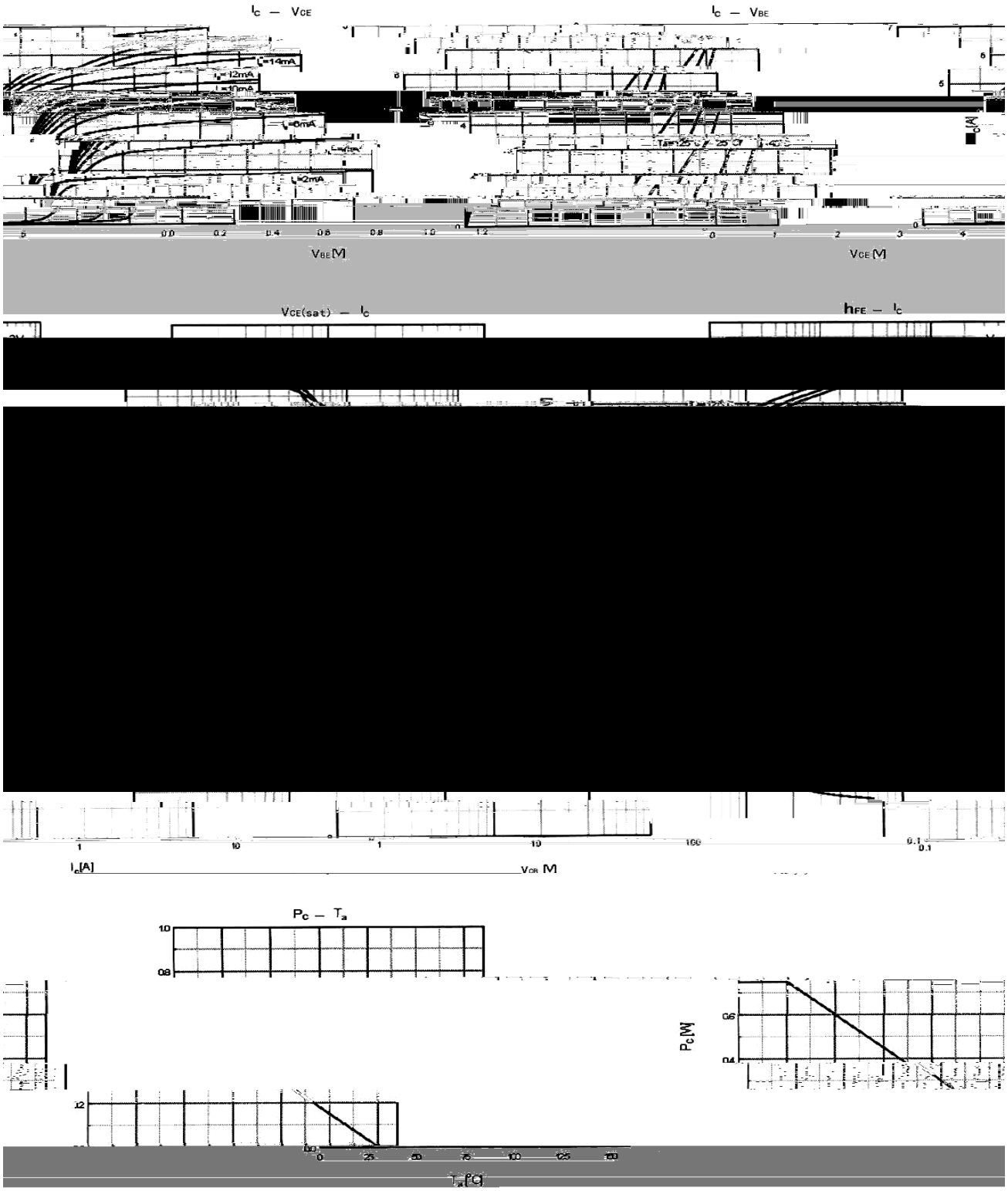
/ Absolute Maximum Ratings(Ta=25)

v ̈Ω Parameter	ϒ N Symbol	̈Ω Ö Rating	D Ч Unit
Collector to Base Voltage	V_{CBO}	40	V
Collector to Emitter Voltage	V_{CEO}	20	V
Emitter to Base Voltage	V_{EBO}	7.0	V
Collector Current - Continuous	I_C	5.0	A
Collector Power Dissipation	P_C	750	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 Ќ 150	

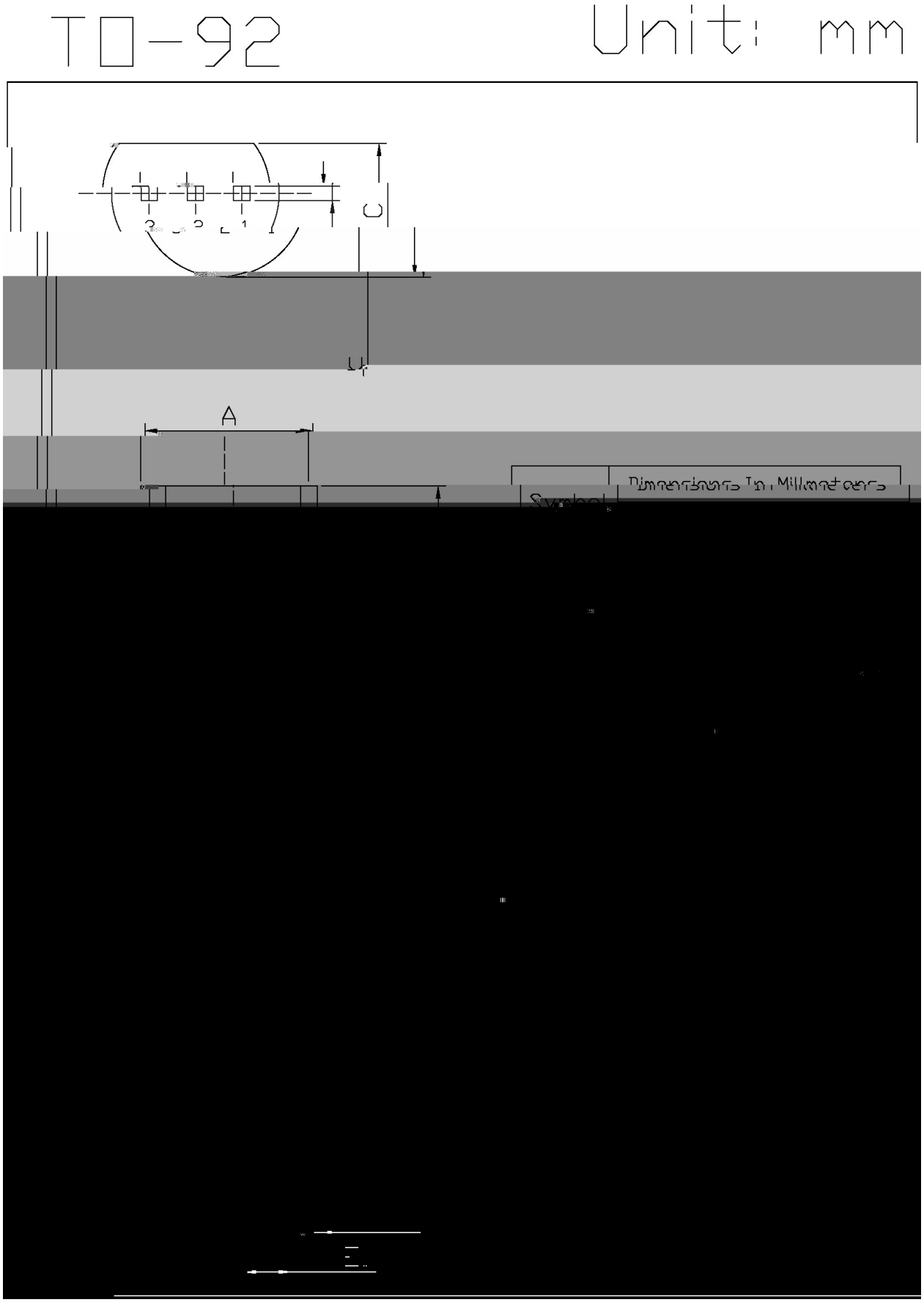
/ Electrical Characteristics(Ta=25)

v ̈Ω Parameter	ϒ N Symbol	╨ ; ̊ Ţ Test Conditions	ѡ ņ Ö Min	Ɛ ʒ Ö Typ	ѡ ᶻ Ö Max	D Ч Unit
Collector to Emitter Breakdown Voltage	V_{CEO}	I_C=1.0mA I_B=0	20			V
Emitter to Base Breakdown Voltage	V_{EBO}	I_E=100μA I_C=0	7			V
Collector Cut-Off Current	I_{CBO}	V_{CB}=10V I_E=0			0.1	μA
Emitter Cut-Off Current	I_{EBO}	V_{EB}=7.0V I_C=0			0.1	μA
DC Current Gain	h_{FE}	V_{CE}=2.0V I_C=0.5A	700	1000		
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=3.0A I_B=0.1A			0.5	V
Base to Emitter Saturation Voltage	$V_{BE(sat)}$	I_C=3.0A I_B=0.1A			1.5	V
Transition Frequency	f_T	V_{CE}=6.0V I_C=50mA		150		MHz
Output Capacitance	C_{ob}	V_{CB}=20V I_E=0 f=1.0MHz		25		pF

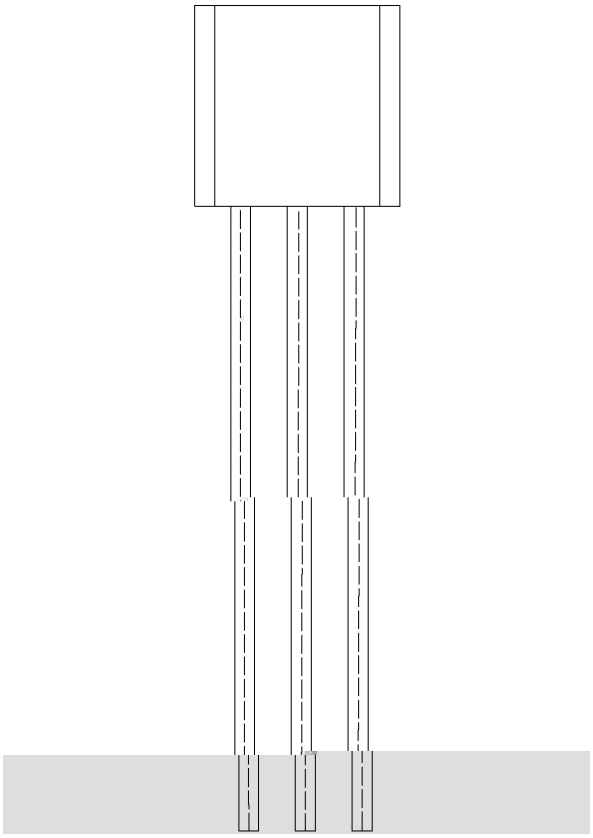
/ Electrical Characteristic Curve



/ Package Dimensions



/ Marking Instructions



ب ˝ χ

EU=

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( ) / Temperature Profile for Dip Soldering(Pb-Free)

ب ˝ χ

1 Ĺ ♬ □ ỷ 25 Ḱ 150 ł ı ̀H ڑ 60 Ḱ 90sec;

2 Š Ө □ ỷ 255 ° 5 ł ı ̀H ڑ ̀Y ሕ 5 ° 0.5sec;

3 ì ˙ Ⴑ ˛ ɔ ѡ ỷ ሕ 2 Ḱ 10 ł /sec.

Note:

1.Preheating:25~150 ł , Time:60~90sec.

2.Peak Temp.:255 ° 5 ł , Duration:5 ° 0.5sec.

3. Cooling Speed: 2~10 ł /sec.

/ Resistance to Soldering Heat Test Conditions

□ ỷ χ 270 ° 5 ł	̀H ڑ χ 10 ° 1 sec.	Temp:270±5	Time:10±1 sec

/ Packaging SPEC.

̈Ω ţ ɣ Ł / BULK

Package Type